

REMARKS

This supplemental preliminary amendment is submitted to correct errors in claim numbering in the list of claims cancelled by the preliminary amendment, and to correctly number the added claims. In addition, the preliminary amendment failed to incorporate two claims from the parent application, which are hereby added.

The related patent data supplied in the preliminary amendment is correct. Accordingly, please incorporate such data into the application. Please disregard all listings of claims in the preliminary amendment and substitute the correct listing of cancelled claims and added claims submitted herein.

Claims 1-32 are cancelled. Claims 33-37 are added. Claims 33-37 are pending in the application. Applicant requests examination of the pending claims.

The added claims 33-37 are fully supported by the specification. With respect to claim 33, support for the claimed subject matter is found in the specification at, for example, page 13, lines 2-13 and Fig. 8. Support for the subject matter of claim 34 is found, for example, at page 9, lines 7-9. With respect to claim 35, support for the claimed subject matter is found at, for instance, page 9, lines 13-5. With respect to claim 36, the subject matter claimed is supported by the specification at, for example, page 11, lines 3-7. With respect to claim 37, the subject matter claimed is supported by the specification at, for example, page 13, lines 11-13.

Priority Appl. No. 09/837,645

Respectfully submitted,

Dated: Oct 8, 2001

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Priority Application Serial No. 09/837,645
Priority Filing Date April 17, 2001
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Assignee Micron Technology, Inc.
Priority Group Art Unit 2813
Priority Examiner Schillinger, L..
Attorney's Docket No. M122-1780
Title: Methods of Forming a Thin Film Transistor

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VERSION WITH MARKINGS TO SHOW CHANGES MADE BY THE
ACCOMPANYING SUPPLEMENTAL PRELIMINARY AMENDMENT

In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 1-32 are cancelled.

33. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:
forming a transistor gate;
forming a polycrystalline thin film transistor layer over the transistor gate;
forming a fluorine containing layer proximate the polycrystalline thin film transistor layer; and
transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

34. (New) The method of claim 33 wherein the polycrystalline thin film transistor layer comprises silicon.

35. (New) The method of claim 33 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing WF_6 and SiH_4 precursors.

36. (New) The method of claim 33 further comprising, after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

37. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

Priority Appl. N . 09/837,645

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